--19. *(Amended)* A method of providing the transistor according to claim 1 comprising:

providing a substantially one-dimensional elongate conducting means by providing a first semiconductor substantially surrounded by a second semiconductor material, the elongate conducting means being provided by creating a groove of second semiconductor such that at least one wall of the groove is a substantially planer surface roughly parallel to a crystal plane on which the growth rate of the first semiconductor is substantially zero and subsequently providing the first semiconductor in the groove,

providing a source electrode at a first end region of the conducting means and a drain electrode at a second end region of the conducting means, and

providing at least one further gate electrode in a region of the conducting means.--